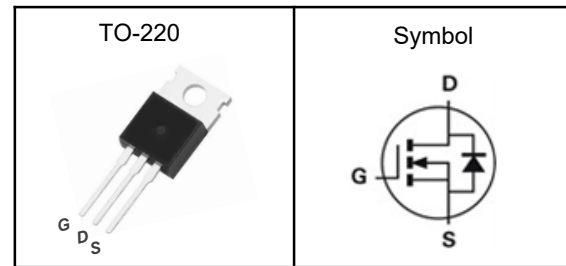


**N-Channel Enhancement Mode MOSFET**
**Features**

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant & Halogen-Free

**Applications**

- Power Management in Desktop Computer
- DC/DC Converters

**Pin Description**


$V_{DSS}$	100	V
$R_{DS(ON)-Typ}$	4.2	m $\Omega$
$I_D$	180	A

**Absolute Maximum Ratings** ( $T_J=25^\circ\text{C}$ , Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
$V_{DSS}$	Drain-Source Voltage	100	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$T_J$	Maximum Junction Temperature	-55 to 175	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
$I_{DM}^{①}$	Pulse Drain Current Tested	650	A
$I_D$	Continuous Drain Current	180	A
$P_D$	Maximum Power Dissipation	350	W
$E_{AS}$	Avalanche Energy, Single pulse	900	mJ

**Thermal Characteristics**

Symbol	Parameter	Rating	Unit
$R_{\theta JA}^{③}$	Thermal Resistance-Junction to Ambient	62.5	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.35	$^\circ\text{C}/\text{W}$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature  $150^\circ\text{C}$ .

Note ③ : Surface Mounted on  $1\text{in}^2$  FR-4 board with 1oz.



<b>N-Channel Enhancement Mode MOSFET</b>
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**Electrical Characteristics** ( $T_J=25^\circ\text{C}$ , Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
<b>Static Electrical Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V$	---	---	1	$\mu A$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	---	4	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=80A$	---	4.2	5.5	m $\Omega$
<b>Dynamic Characteristics<sup>⑤</sup></b>						
$C_{iss}$	Input Capacitance	$V_{DS}=50V,$ $V_{GS}=0V,$ Freq.=1MHz	---	8950	---	pF
$C_{oss}$	Output Capacitance		---	620	---	
$C_{rss}$	Reverse Transfer Capacitance		---	245	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DS}=60V, V_{GS}=10V,$ $I_D=30A, R_G=2.8\Omega$	---	26	---	nS
$T_r$	Turn-on Rise Time		---	70	---	
$T_{d(off)}$	Turn-off Delay Time		---	76	---	
$T_f$	Turn-off Fall Time		---	90	---	
$Q_g$	Total Gate Charge	$V_{DS}=50V, V_{GS}=10V,$ $I_D=75A$	---	150	---	nC
$Q_{gs}$	Gate-Source Charge		---	36	---	
$Q_{gd}$	Gate-Drain Charge		---	40	---	
<b>Source-Drain Characteristics</b>						
$V_{SD}$	Diode Forward Voltage	$I_S=80A, V_{GS}=0V$	---	---	1.3	V
$t_{rr}$	Reverse Recovery Time	$I_S=75A, V_{GS}=0V,$ $di_F/dt=100A/\mu s$	---	65	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	125	---	nC

Note ④ : Pulse test (pulse width $\leq 300\mu s$ , duty cycle $\leq 2\%$ ).

Note ⑤ : Guaranteed by design, not subject to production testing.

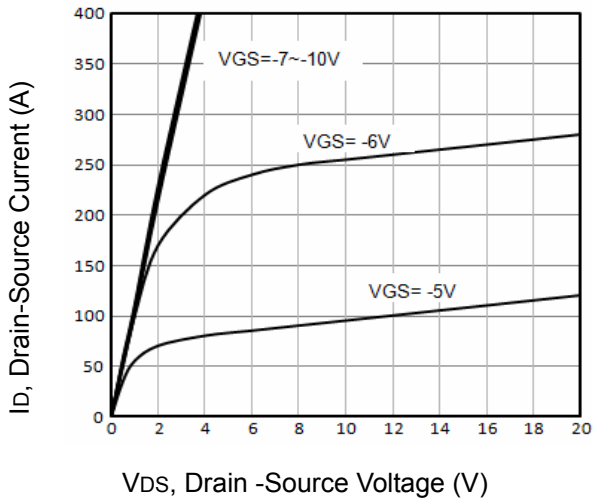
**N-Channel Enhancement Mode MOSFET**
**Typical Characteristics**


Fig1. Typical Output Characteristics

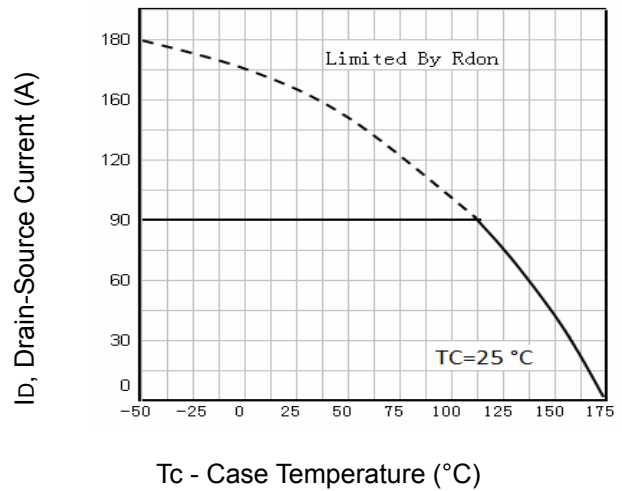


Fig2. Maximum Drain Current Vs. Case Temperature

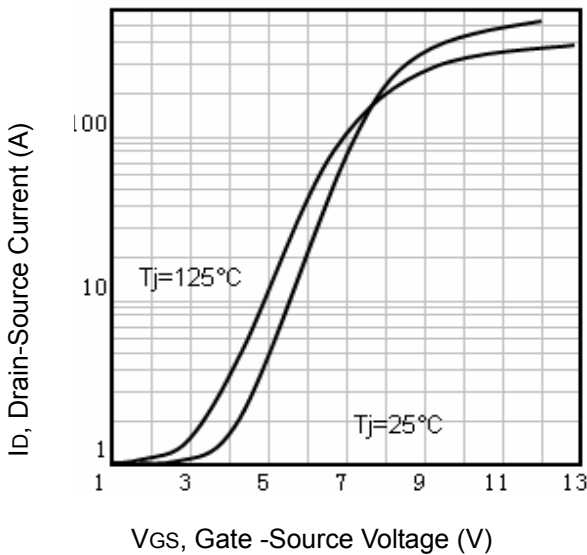


Fig3. Typical Transfer Characteristics

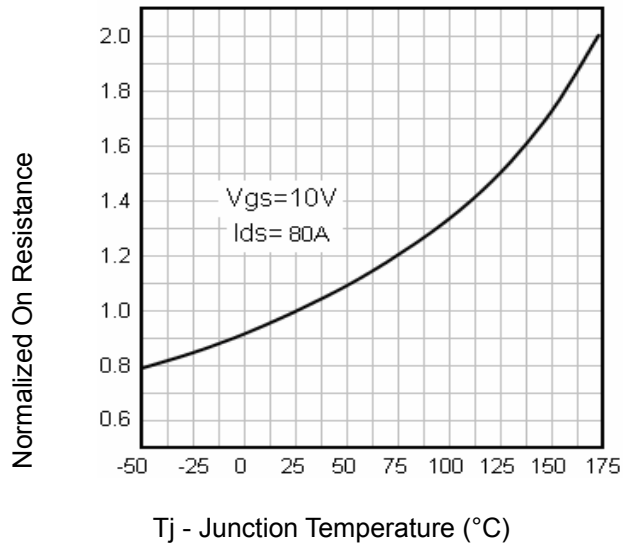


Fig4. Normalized On-Resistance Vs. Temperature

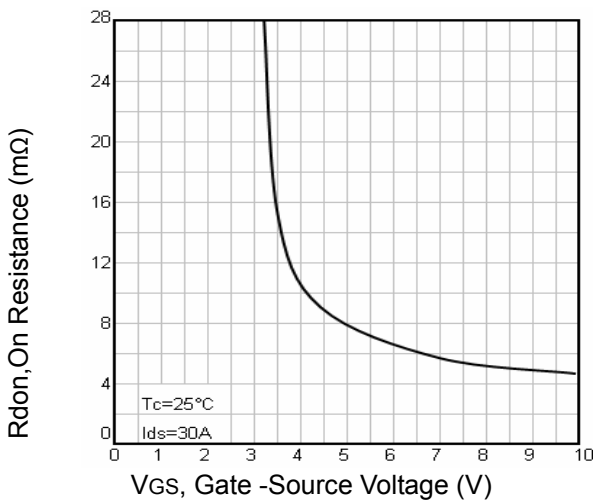


Fig5. Typical On-Resistance Vs. Gate-Source Voltage

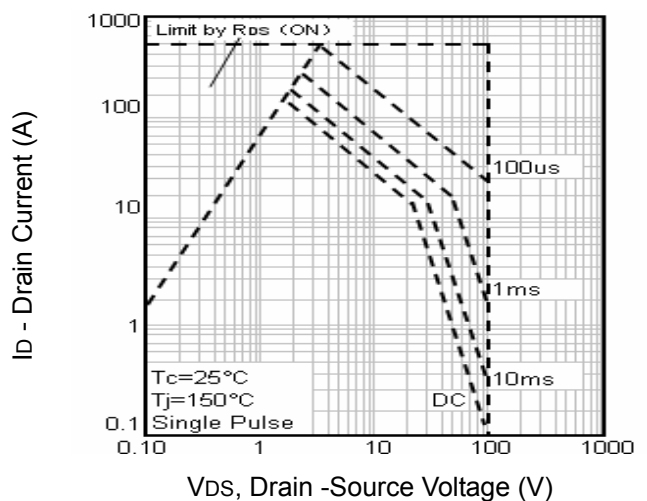


Fig6. Maximum Safe Operating Area

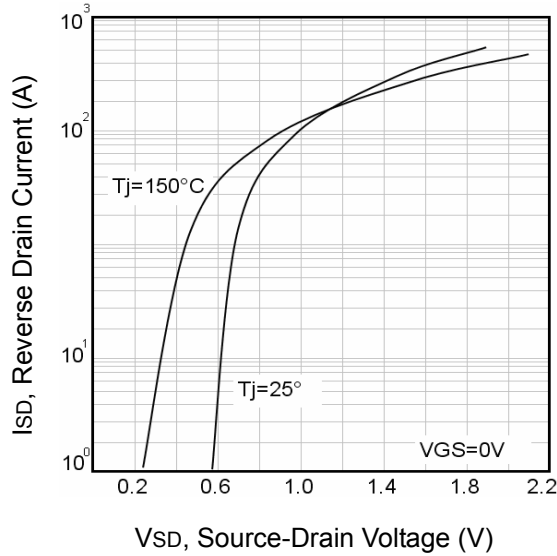
**N-Channel Enhancement Mode MOSFET**


Fig7. Typical Source-Drain Diode Forward Voltage

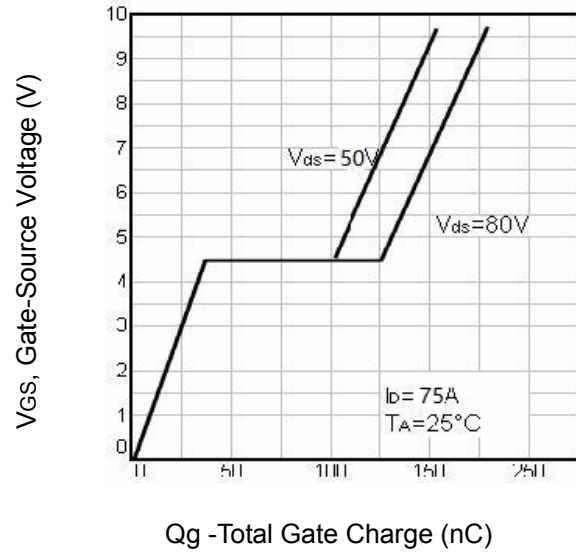


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

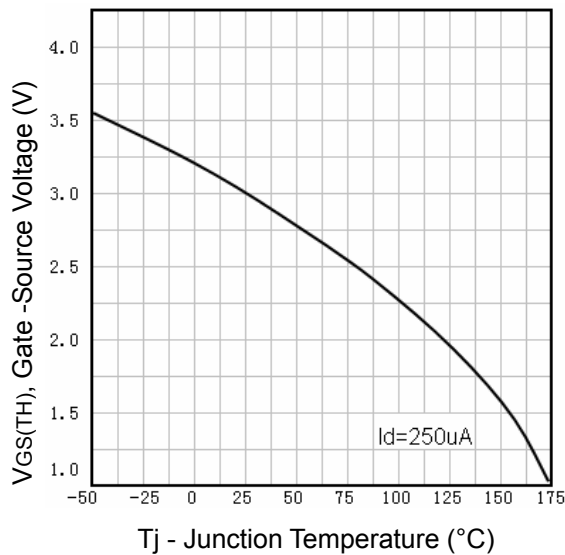


Fig9. Threshold Voltage Vs. Temperature

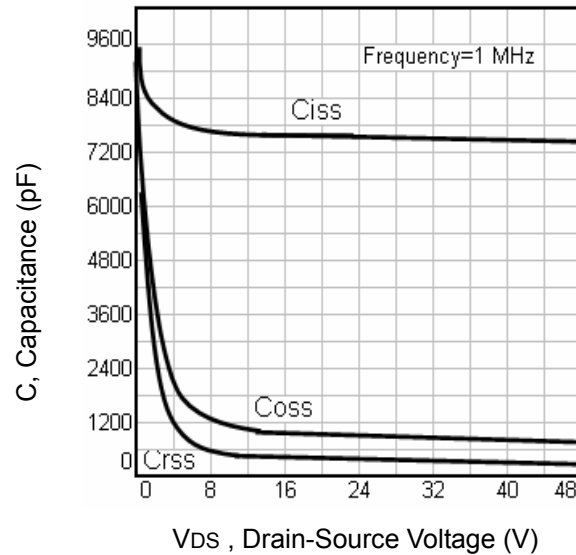
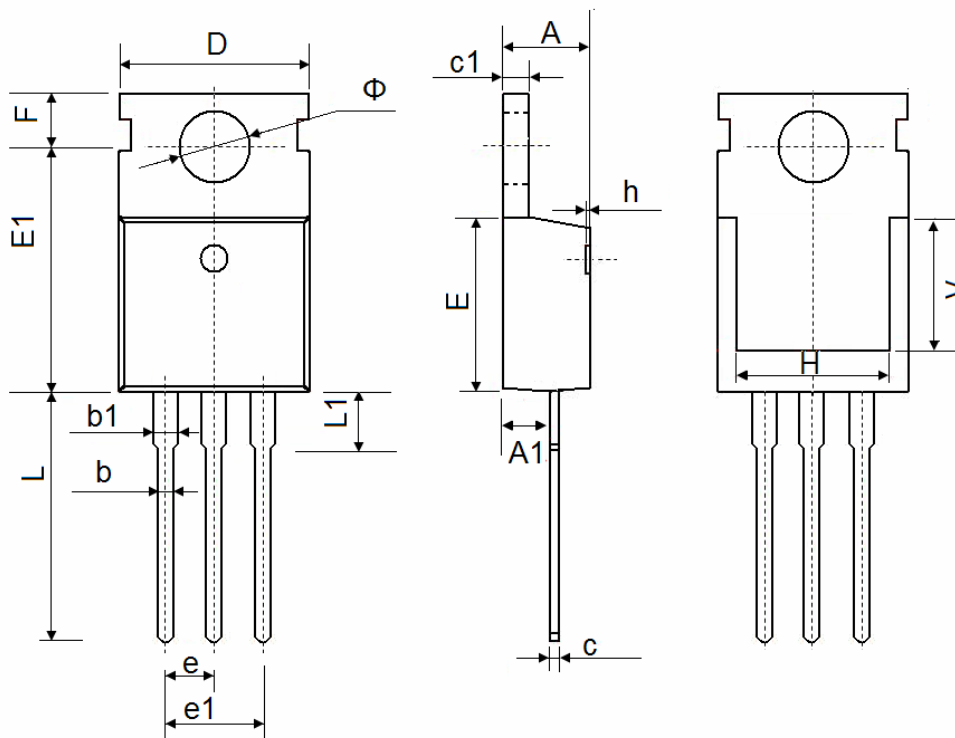


Fig10. Typical Capacitance Vs. Drain-Source Voltage

**N-Channel Enhancement Mode MOSFET**
**TO-220 Package Outline Data**


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.350	4.650
A1	2.250	2.550
b	0.710	0.910
b1	1.170	1.400
c	0.330	0.650
c1	1.200	1.400
D	9.910	10.250
E	8.9500	9.750
E1	12.650	12.950
e	2.540 TYP.	
e1	4.980	5.180
F	2.650	2.950
H	7.900	8.100
h	0.000	0.300
L	12.700	13.500
L1	2.850	3.250
V	7.500 REF.	
Φ	3.400	3.800